

AMENDMENT TRANSMITTAL LETTER

Docket No.
M4065.0319/P319Application No.
09/296,835Filing Date
April 22, 1999Examiner
Erik KielinArt Unit
2813

Applicant(s): Ronald A. Weimer, et al.


Invention: FABRICATION OF DRAM AND OTHER SEMICONDUCTOR DEVICES WITH AN
INSULATING FILM USING A WET RAPID THERMAL OXIDATION PROCESS

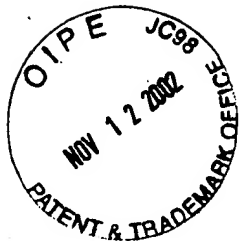
TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	14	- 40 =		x	0.00
Independent Claims	7	- 8 =		x	0.00
Multiple Dependent Claims (check if applicable)				<input type="checkbox"/>	
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					

☒ Large Entity☐ Small Entity☐ No additional fee is required for this amendment.☐ Please charge Deposit Account No. _____ in the amount of \$ _____.
A duplicate copy of this sheet is enclosed.☐ A check in the amount of \$ _____ to cover the filing fee is enclosed.☐ Payment by credit card. Form PTO-2038 is attached.☒ The Commissioner is hereby authorized to charge and credit Deposit Account No. 04-1073
as described below. A duplicate copy of this sheet is enclosed.☒ Credit any overpayment.☒ Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.
Thomas J. D'Amico
Attorney Reg. No.: 28,371Dated: November 12, 2002DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP
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(PATENT) *Mollish*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Ronald A. Weimer, et al.

Application No.: 09/296,835

Group Art Unit: 2813

Filed: April 22, 1999

Examiner: Erik Kielin

For: FABRICATION OF DRAM AND OTHER
SEMICONDUCTOR DEVICES WITH AN
INSULATING FILM USING A WET
RAPID THERMAL OXIDATION PROCESS

AMENDMENT

BOX: Non-Fee Amendment
Commissioner for Patents
Washington, DC 20231

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Dear Sir:

This paper is responsive to the Office Action dated August 12, 2002, rejecting claims 2-5, 8, 10-12, and 42-44. Please amend the above-captioned U.S. Patent application as follows:

IN THE CLAIMS:

Please replace claims with 8 and 42-44 with amended claims 8 and 42-44 below.

F1 *SUB* 8. (five times amended) A method of fabricating a semiconductor device comprising:

depositing an oxygen-deficient dielectric film having a dielectric constant of at least about 25 over an underlying layer;

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01 FC:1202 54.00 CH
02 FC:1701 336.00 CH